Supplementary information

Transition Pathway Between Gyroid and Cylindrical Morphology in Linear

Triblock Terpolymer Thin Films

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Figure SI-1: TEM of a bulk specimen of the ISP sample staining by OsO_4 and I_2 used in this study showing typical hallmarks of (111) plane of a G_A structure



Figure SI-2: Top-view TEM image of a ISP thin film annealed for 4 hours and selectively stained by OsO₄. Rectangle shows the lattice unit.



Figure SI-3: Side-view of different possible orientations of a G_A morphology having the (011) plane parallel to the surface following [01-1] (a), [11-1] (b), [21-1] (c), [100] (d) directions, assuming a cubic lattice where a = b = c and $\alpha = \beta = \gamma = 90^{\circ}$.



Figure SI-4: Schematic view of the deformation of the ideal cubic lattice into the actual lattice

deformed during film drying.



Figure SI-5: Actual top view (011) plane (a) and side view (100) plane (b) of the skeletal model





Figure SI-6: Configuration of the GISAXS experiment



Figure SI-7: 2D GISAXS pattern of figure 3 after (a) UVO treatment and (b) staining by I_2



Figure SI-8: schematic side view image of the arrangement of the network restricted to the layer

near the air surface (probed by AFM).



Figure SI-9: TEM cross-sectional images of solvent annealed (24 h) thin films after staining by

 $OsO_4 \ and \ I_2.$



Figure SI-10: schematic representation of the cylindrical structure arranged in a P2mm space group after transitioning from the G_A phase : side view ((010) plane)(a) and top view ((001) plane) (b). PI is in green and PVP in red .



Figure SI-11: 2D GISAXS pattern of figure 6 (P2mm structure) after UVO treatment (a) and selective staining by I_2 (b).